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Kind regards,

Team Nexperia



## **BC846BS**

# 65 V, 100 mA NPN/NPN general-purpose transistor Rev. 01 — 24 August 2009 Produ

**Product data sheet** 

## 1. Product profile

#### 1.1 General description

NPN/NPN general-purpose transistor pair in a very small Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview** 

Type number	Package I			NPN/PNP
	NXP	JEITA	complement	complement
BC846BS	SOT363	SC-88	BC856BS	BC846BPN

#### 1.2 Features

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and board space
- No mutual interference between the transistors
- AEC-Q101 qualified

#### 1.3 Applications

■ General-purpose switching and amplification

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
$V_{CEO}$	collector-emitter voltage	open base	-	-	65	V
I <sub>C</sub>	collector current		-	-	100	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$	200	300	450	



#### 65 V, 100 mA NPN/NPN general-purpose transistor

## 2. Pinning information

Table 3. Pinning

Table 5.	i iiiiiiig		
Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1	G. G. G.	
2	base TR1	6 5 4	6 5 4
3	collector TR2		TR2
4	emitter TR2	0	(TR1)
5	base TR2	∐1 ∐2 ∐3	
6	collector TR1		1 2 3
			sym020

## 3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
BC846BS	SC-88	plastic surface-mounted package; 6 leads	SOT363

## 4. Marking

Table 5. Marking codes

Type number	Marking code[1]
BC846BS	*E5

[1] \* = -: made in Hong Kong

\* = p: made in Hong Kong

\* = t: made in Malaysia

\* = W: made in China

## 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit				
Per transist	Per transistor								
$V_{CBO}$	collector-base voltage	open emitter	-	80	V				
$V_{CEO}$	collector-emitter voltage	open base	-	65	V				
$V_{EBO}$	emitter-base voltage	open collector	-	6	V				
I <sub>C</sub>	collector current		-	100	mA				
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA				
I <sub>BM</sub>	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u> _	200	mW				

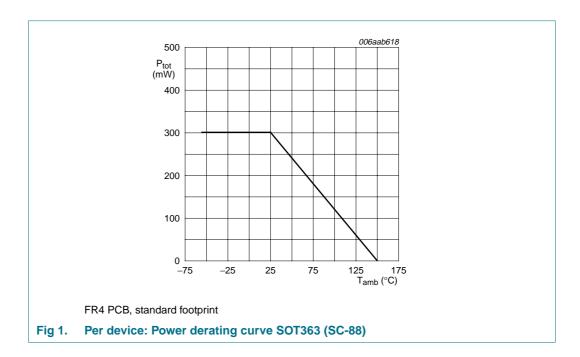
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#### 65 V, 100 mA NPN/NPN general-purpose transistor

**Table 6.** Limiting values ...continued In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per device					
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u> -	300	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



#### 6. Thermal characteristics

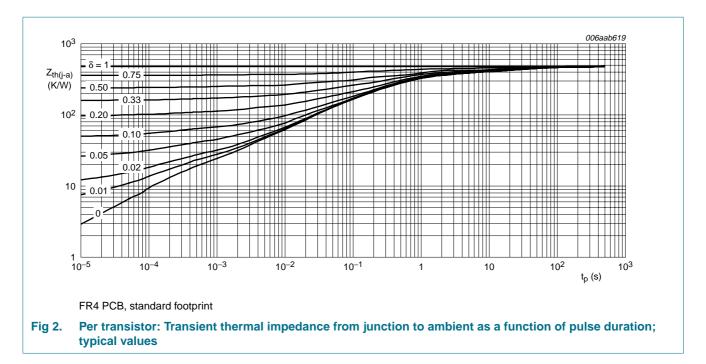
Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	625	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	230	K/W
Per device	•					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	416	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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#### 65 V, 100 mA NPN/NPN general-purpose transistor



## 7. Characteristics

Table 8. Characteristics

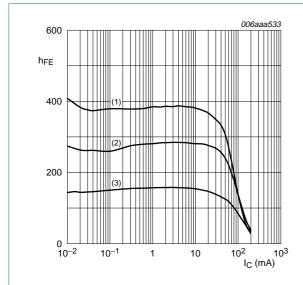
 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	15	nA
	current	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 ^{\circ}\text{C}$	-	-	5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 6 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V				
		I <sub>C</sub> = 10 μA	-	280	-	
		$I_C = 2 \text{ mA}$	200	300	450	
$V_{CEsat}$	collector-emitter	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	55	100	mV
	saturation voltage	$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$	-	200	300	mV
$V_{BEsat}$	base-emitter	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	755	850	mV
	saturation voltage	$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$	-	1000	-	mV
$V_{BE}$	base-emitter voltage	V <sub>CE</sub> = 5 V				
		$I_C = 2 \text{ mA}$	580	650	700	mV
		I <sub>C</sub> = 10 mA	-	-	770	mV

#### 65 V, 100 mA NPN/NPN general-purpose transistor

Table 8. Characteristics ... continued  $T_{amb} = 25 \,^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0 \text{ A};$ f = 1 MHz	-	1.9	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = I_c = 0 \text{ A};$ f = 1 MHz	-	11	-	pF
f <sub>T</sub>	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	100	-	-	MHz
NF	noise figure	$\begin{split} &V_{CE}=5~V;~I_{C}=0.2~\text{mA};\\ &R_{S}=2~k\Omega;\\ &f=10~\text{Hz}~\text{to}~15.7~\text{kHz} \end{split}$	-	1.9	-	dB
		$\begin{split} &V_{CE}=5 \text{ V; } I_{C}=0.2 \text{ mA;} \\ &R_{S}=2 \text{ k}\Omega; f=1 \text{ kHz;} \\ &B=200 \text{ Hz} \end{split}$	-	3.1	-	dB



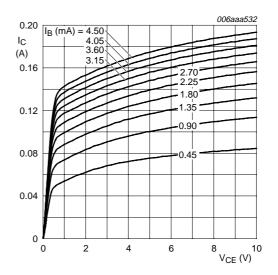
 $V_{CE} = 5 V$ 

(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \,^{\circ}C$ 

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 3. Per transistor: DC current gain as a function of collector current; typical values

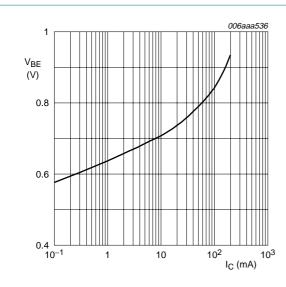


 $T_{amb} = 25 \, ^{\circ}C$ 

Fig 4. Per transistor: Collector current as a function of collector-emitter voltage; typical values

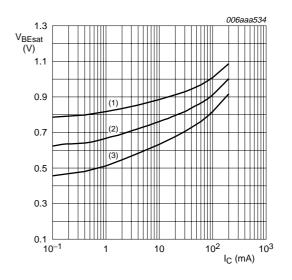
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#### 65 V, 100 mA NPN/NPN general-purpose transistor



 $V_{CE} = 5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$ 

Fig 5. Per transistor: Base-emitter voltage as a function of collector current; typical values



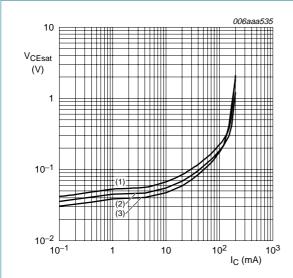
 $I_{\rm C}/I_{\rm B} = 20$ 

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 6. Per transistor: Base-emitter saturation voltage as a function of collector current; typical values



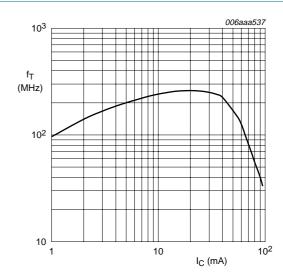
 $I_C/I_B = 20$ 

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 7. Per transistor: Collector-emitter saturation voltage as a function of collector current; typical values



 $V_{CE} = 5 \text{ V}; T_{amb} = 25 \,^{\circ}\text{C}$ 

Fig 8. Per transistor: Transition frequency as a function of collector current; typical values

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#### 65 V, 100 mA NPN/NPN general-purpose transistor

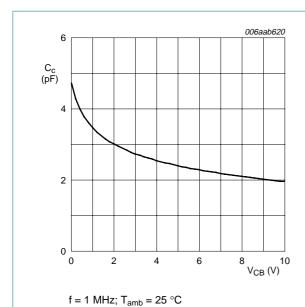


Fig 9. Per transistor: Collector capacitance as a function of collector-base voltage; typical values

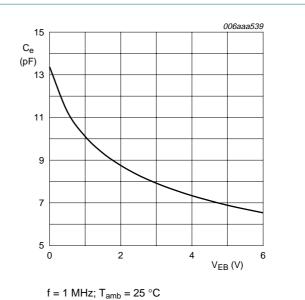


Fig 10. Per transistor: Emitter capacitance as a function of emitter-base voltage; typical values

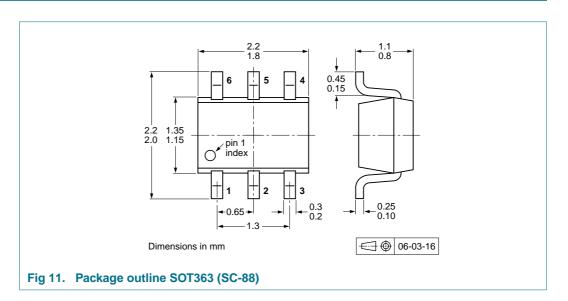
65 V, 100 mA NPN/NPN general-purpose transistor

#### 8. Test information

#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 9. Package outline



## 10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packing quantity	
				3000	10000
BC846BS	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-165

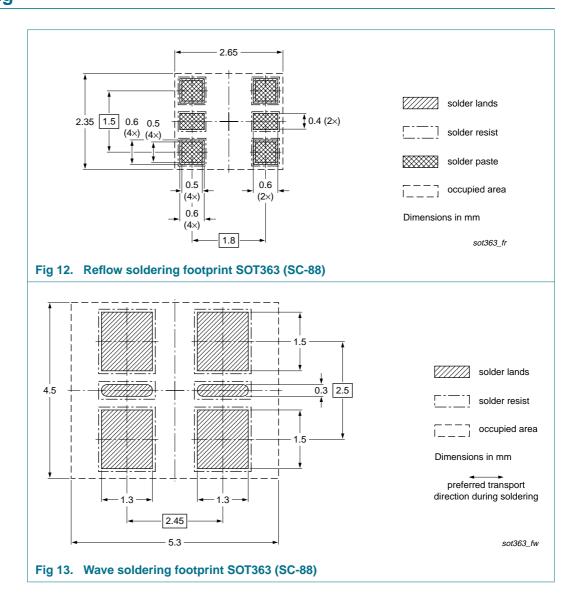
<sup>[1]</sup> For further information and the availability of packing methods, see  $\underline{\text{Section 14}}$ .

[2] T1: normal taping

[3] T2: reverse taping

#### 65 V, 100 mA NPN/NPN general-purpose transistor

## 11. Soldering



## 65 V, 100 mA NPN/NPN general-purpose transistor

## 12. Revision history

#### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC846BS_1	20090824	Product data sheet	-	-

#### 65 V, 100 mA NPN/NPN general-purpose transistor

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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